

L Number	Hits	Search Text	DB	Time stamp
-	19	(SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH) and ("isopropyl alcohol" or IPA)	USPAT; US-PGPUB	2003/04/24 12:02
-	16	((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH) and ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/15 11:42
-	5	((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH) and ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109) and 438/\$.ccls.	USPAT; US-PGPUB	2003/04/09 15:50
-	182	(SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH)	USPAT; US-PGPUB	2003/04/24 12:02
-	507	(SiON or "silicon oxynitride") and ("isopropyl alcohol" or IPA)	USPAT; US-PGPUB	2003/04/09 15:50
-	0	438/692.ccls. and ((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH))	USPAT; US-PGPUB	2003/04/09 15:50
-	1	438/692.ccls. AND ((SiON or "silicon oxynitride") and ("isopropyl alcohol" or IPA))	USPAT; US-PGPUB	2003/04/09 15:52
-	89	438/749.ccls.	USPAT; US-PGPUB	2003/04/09 15:53
-	1	((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH)) and 438/749.ccls.	USPAT; US-PGPUB	2003/04/09 15:54
-	0	((SiON or "silicon oxynitride") and ("isopropyl alcohol" or IPA)) and 438/749.ccls.	USPAT; US-PGPUB	2003/04/09 15:54
-	160	438/750.ccls.	USPAT; US-PGPUB	2003/04/09 15:55
-	0	((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH)) and 438/750.ccls.	USPAT; US-PGPUB	2003/04/09 15:55
-	0	((SiON or "silicon oxynitride") and ("isopropyl alcohol" or IPA)) and 438/750.ccls.	USPAT; US-PGPUB	2003/04/09 15:55
-	110	438/751.ccls.	USPAT; US-PGPUB	2003/04/09 15:55
-	0	((SiON or "silicon oxynitride") and ("isopropyl alcohol" or IPA)) and 438/751.ccls.	USPAT; US-PGPUB	2003/04/09 15:55
-	1	((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH)) and 438/751.ccls.	USPAT; US-PGPUB	2003/04/09 15:56
-	361	438/906.ccls.	USPAT; US-PGPUB	2003/04/09 15:56
-	0	((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH)) and 438/906.ccls.	USPAT; US-PGPUB	2003/04/09 15:56
-	2	((SiON or "silicon oxynitride") and ("isopropyl alcohol" or IPA)) and 438/906.ccls.	USPAT; US-PGPUB	2003/04/09 16:03
-	293	438/974.ccls.	USPAT; US-PGPUB	2003/04/09 16:03
-	0	((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH)) and 438/974.ccls.	USPAT; US-PGPUB	2003/04/09 16:03
-	0	((SiON or "silicon oxynitride") and ("isopropyl alcohol" or IPA)) and 438/974.ccls.	USPAT; US-PGPUB	2003/04/09 16:03
-	821	(SiON or "silicon oxynitride") and hydrophobic	USPAT; US-PGPUB	2003/04/09 16:04
-	86	438/\$.ccls. and ((SiON or "silicon oxynitride") and hydrophobic)	USPAT; US-PGPUB	2003/04/09 16:04
-	72	(438/\$.ccls. and ((SiON or "silicon oxynitride") and hydrophobic)) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/09 16:04
-	43622	platen	USPAT; US-PGPUB	2003/04/09 16:04
-	1	((438/\$.ccls. and ((SiON or "silicon oxynitride") and hydrophobic)) not (@ad>20020109 or @rlad>20020109)) and platen	USPAT; US-PGPUB	2003/04/09 16:05
-	5	(SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH) and platen	USPAT; US-PGPUB	2003/04/09 16:07
-	5	((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH) and platen) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/09 16:05
-	10	(SiON or "silicon oxynitride") and ("isopropyl alcohol" or IPA) and platen	USPAT; US-PGPUB	2003/04/09 16:07

-	9	((SiON or "silicon oxynitride") and ("isopropyl alcohol" or IPA) and platen) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/09 17:01
-	24	438/for.111.ccls.	EPO; JPO; DERWENT	2003/04/10 09:54
-	571	remov\$3 with (SiON or "silicon oxynitride")	USPAT; US-PGPUB	2003/04/10 10:42
-	19	(remov\$3 with (SiON or "silicon oxynitride")) and ("tetramethyl ammonium hydroxide" or TMAH)	USPAT; US-PGPUB	2003/04/10 10:43
-	17	((remov\$3 with (SiON or "silicon oxynitride")) and ("tetramethyl ammonium hydroxide" or TMAH)) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/15 11:57
-	4	(remov\$3 with (SiON or "silicon oxynitride")) and ("isopropyl alcohol" or IPA)	USPAT; US-PGPUB	2003/04/10 10:46
-	4	((remov\$3 with (SiON or "silicon oxynitride")) and ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/15 11:57
-	14469	(polish\$3 or CMP) with (partial or partially or thickness)	USPAT; US-PGPUB	2003/04/15 11:59
-	391	438/626.ccls.	USPAT; US-PGPUB	2003/04/15 11:37
-	73	((polish\$3 or CMP) with (partial or partially or thickness)) and 438/626.ccls.	USPAT; US-PGPUB	2003/04/15 11:38
-	20	(SiON or "silicon oxynitride") and (((polish\$3 or CMP) with (partial or partially or thickness)) and 438/626.ccls.)	USPAT; US-PGPUB	2003/04/15 11:38
-	0	((SiON or "silicon oxynitride") with ("tetramethyl ammonium hydroxide" or TMAH) and ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/15 12:00
-	0	((SiON or "silicon oxynitride") same ("tetramethyl ammonium hydroxide" or TMAH) and ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/15 11:43
-	16	((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH) and ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/15 11:49
-	0	((polish\$3 or CMP) with (partial or partially or thickness)) and (((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH) and ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109))	USPAT; US-PGPUB	2003/04/15 11:43
-	44880	((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH) or ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/15 11:44
-	375	((polish\$3 or CMP) with (partial or partially or thickness)) and (((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH) or ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109))	USPAT; US-PGPUB	2003/04/15 11:44
-	23	(SiON or "silicon oxynitride") and (((polish\$3 or CMP) with (partial or partially or thickness)) and (((SiON or "silicon oxynitride") and ("tetramethyl ammonium hydroxide" or TMAH) or ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109)))	USPAT; US-PGPUB	2003/04/15 11:47
-	582	438/633.ccls.	USPAT; US-PGPUB	2003/04/15 11:47
-	47	((polish\$3 or CMP) with (partial or partially or thickness)) and (SiON or "silicon oxynitride") and 438/633.ccls.	USPAT; US-PGPUB	2003/04/15 11:47
-	50081	("tetramethyl ammonium hydroxide" or TMAH) or ("isopropyl alcohol" or IPA)	USPAT; US-PGPUB	2003/04/15 11:50
-	1	((polish\$3 or CMP) with (partial or partially or thickness)) and (SiON or "silicon oxynitride") and 438/633.ccls.) and ("tetramethyl ammonium hydroxide" or TMAH) or ("isopropyl alcohol" or IPA))	USPAT; US-PGPUB	2003/04/15 11:51
-	1429	438/692.ccls.	USPAT; US-PGPUB	2003/04/15 11:51
-	1	(("tetramethyl ammonium hydroxide" or TMAH) or ("isopropyl alcohol" or IPA)) and (((polish\$3 or CMP) with (partial or partially or thickness)) and (SiON or "silicon oxynitride") and 438/692.ccls.)	USPAT; US-PGPUB	2003/04/15 11:51
-	41	((polish\$3 or CMP) with (partial or partially or thickness)) and (SiON or "silicon oxynitride") and 438/692.ccls.	USPAT; US-PGPUB	2003/04/15 11:55

-	751	438/672.ccls.	USPAT; US-PGPUB	2003/04/15 11:55
-	0	((("tetramethyl ammonium hydroxide" or TMAH) or ("isopropyl alcohol" or IPA)) and (((polish\$3 or CMP) with (partial or partially or thickness)) and (SiON or "silicon oxynitride")) and 438/672.ccls.)	USPAT; US-PGPUB	2003/04/15 11:55
-	17	((polish\$3 or CMP) with (partial or partially or thickness)) and (SiON or "silicon oxynitride") and 438/672.ccls.	USPAT; US-PGPUB	2003/04/15 11:55
-	0	((remov\$3 with (SiON or "silicon oxynitride"))with ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/15 11:58
-	0	((remov\$3 with (SiON or "silicon oxynitride")) with ("tetramethyl ammonium hydroxide" or TMAH)) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/15 11:59
-	1201	438/for.355.ccls.	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 11:58
-	0	((remov\$3 with (SiON or "silicon oxynitride"))with ("isopropyl alcohol" or IPA)) not (@ad>20020109 or @rlad>20020109)	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 11:59
-	0	((remov\$3 with (SiON or "silicon oxynitride")) with ("tetramethyl ammonium hydroxide" or TMAH)) not (@ad>20020109 or @rlad>20020109)	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 11:59
-	5910	(polish\$3 or CMP) with (partial or partially or thickness)	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 11:59
-	2	438/for.355.ccls. and ((polish\$3 or CMP) with (partial or partially or thickness))	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 11:59
-	6548	(SiON or "silicon oxynitride") with ("tetramethyl ammonium hydroxide" or TMAH)or ("isopropyl alcohol" or IPA)	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 12:05
-	0	438/for.355.ccls. and ((SiON or "silicon oxynitride") with ("tetramethyl ammonium hydroxide" or TMAH)or ("isopropyl alcohol" or IPA))	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 12:00
-	8	((polish\$3 or CMP) with (partial or partially or thickness)) and ((SiON or "silicon oxynitride") with ("tetramethyl ammonium hydroxide" or TMAH)or ("isopropyl alcohol" or IPA))	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 12:04
-	952640	semiconductor or "integrated circuit"	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 12:04
-	569	((SiON or "silicon oxynitride") with ("tetramethyl ammonium hydroxide" or TMAH)or ("isopropyl alcohol" or IPA)) and (semiconductor or "integrated circuit")	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 12:04
-	3644	SiON or "silicon oxynitride"	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 12:05
-	0	((((SiON or "silicon oxynitride") with ("tetramethyl ammonium hydroxide" or TMAH)or ("isopropyl alcohol" or IPA)) and (semiconductor or "integrated circuit")) and (SiON or "silicon oxynitride"))	EPO; JPO; DERWENT; IBM_TDB	2003/04/15 12:05
-	13466	SiON or "silicon oxynitride"	USPAT; US-PGPUB	2003/04/24 12:02
-	1824548	remov\$3 or etch\$3	USPAT; US-PGPUB	2003/04/24 12:21
-	1918183	remov\$3 or etch\$3 or clean\$3	USPAT; US-PGPUB	2003/04/24 12:21
-	1655	(SiON or "silicon oxynitride") with (remov\$3 or etch\$3 or clean\$3)	USPAT; US-PGPUB	2003/04/24 12:13
-	1474	((SiON or "silicon oxynitride") with (remov\$3 or etch\$3 or clean\$3)) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/24 12:14
-	64587	438/\$.ccls.	USPAT; US-PGPUB	2003/04/24 12:15
-	1055	((((SiON or "silicon oxynitride") with (remov\$3 or etch\$3 or clean\$3)) not (@ad>20020109 or @rlad>20020109)) and 438/\$.ccls.	USPAT; US-PGPUB	2003/04/24 12:18

-	1436	438/692.ccls.	USPAT; US-PGPUB	2003/04/24 12:16
-	32	(((SiON or "silicon oxynitride") with (remov\$3 or etch\$3 or clean\$3)) not (@ad>20020109 or @rlad>20020109)) and 438/\$.ccls.) and 438/692.ccls.	USPAT; US-PGPUB	2003/04/24 12:16
-	4401	"tetramethyl ammonium hydroxide" or TMAH	USPAT; US-PGPUB	2003/04/24 12:17
-	46457	"isopropyl alcohol" or IPA	USPAT; US-PGPUB	2003/04/24 12:17
-	0	(((SiON or "silicon oxynitride") with (remov\$3 or etch\$3 or clean\$3)) not (@ad>20020109 or @rlad>20020109)) with ("tetramethyl ammonium hydroxide" or TMAH)	USPAT; US-PGPUB	2003/04/24 12:18
-	0	(((SiON or "silicon oxynitride") with (remov\$3 or etch\$3 or clean\$3)) not (@ad>20020109 or @rlad>20020109)) with ("isopropyl alcohol" or IPA)	USPAT; US-PGPUB	2003/04/24 12:18
-	98856	hydrophobic	USPAT; US-PGPUB	2003/04/24 12:19
-	3	(((SiON or "silicon oxynitride") with (remov\$3 or etch\$3 or clean\$3)) not (@ad>20020109 or @rlad>20020109)) with hydrophobic	USPAT; US-PGPUB	2003/04/24 12:20
-	1780212	remov\$3	USPAT; US-PGPUB	2003/04/24 12:22
-	582	(SiON or "silicon oxynitride") with remov\$3	USPAT; US-PGPUB	2003/04/24 12:22
-	532	((SiON or "silicon oxynitride") with remov\$3) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/24 12:22
-	13466	SiON or "silicon oxynitride"	USPAT; US-PGPUB	2003/04/24 12:24
-	1780212	remov\$3	USPAT; US-PGPUB	2003/04/24 12:24
-	944483	slurry or solution	USPAT; US-PGPUB	2003/04/24 12:25
-	964464	W or tungsten	USPAT; US-PGPUB	2003/04/24 14:07
-	46	(SiON or "silicon oxynitride") with remov\$3 with (slurry or solution)	USPAT; US-PGPUB	2003/04/24 14:25
-	2	(W or tungsten) with ((SiON or "silicon oxynitride") with remov\$3 with (slurry or solution))	USPAT; US-PGPUB	2003/04/24 14:07
-	123	conductive and dielectric and "silicon oxynitride" and "titanium nitride" and (via or hole or opening or trench) and tungsten and CMP and slurry	USPAT; US-PGPUB	2003/04/24 14:27
-	107822	@ad>20020109 or @rlad>20020109	USPAT; US-PGPUB	2003/04/24 14:28
-	113	(conductive and dielectric and "silicon oxynitride" and "titanium nitride" and (via or hole or opening or trench) and tungsten and CMP and slurry) not (@ad>20020109 or @rlad>20020109)	USPAT; US-PGPUB	2003/04/24 14:54
-	449	platen with "polishing pad" with slurry	USPAT; US-PGPUB	2003/04/24 15:47
-	0	((SiON or "silicon oxynitride") with remov\$3 with (slurry or solution)) and (platen with "polishing pad" with slurry)	USPAT; US-PGPUB	2003/04/24 15:47
-	2	(conductive and dielectric and "silicon oxynitride" and "titanium nitride" and (via or hole or opening or trench) and tungsten and CMP and slurry) and (platen with "polishing pad" with slurry)	USPAT; US-PGPUB	2003/04/24 15:48